2SJ0582

Silicon P-channel power MOSFET

■ Features

- Avalanche energy capability guaranteed
- High-speed switching
- No secondary breakdown

Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Drain-source surrender voltage	V _{DSS}	-200	V	
Gate-source surrender voltage	V _{GSS}	±20	V	
Drain current	I_{D}	±2	A	
Peak drain current	I_{DP}	±4	A	
Avalanche energy capability *	EAS	10	mJ	
Power dissipation	P_{D}	10	W	
$T_a = 25^{\circ}C$		1		
Channel temperature	T _{ch}	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

Note) *: L = 5 mH, $I_L = 2$ A, 1 pulse

■ Package

• Code U-G2

• Pin Name

1: Gate

2: Drain

3: Source

■ Marking Symbol: J0582

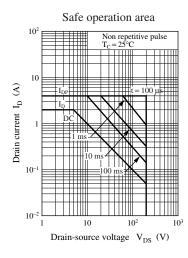
■ Internal Connection

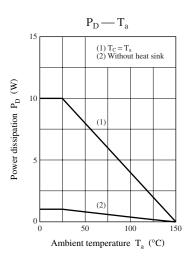


■ Electrical Characteristics $T_C = 25$ °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source cutoff current	I _{DSS}	$V_{DS} = -160 \text{ V}, V_{GS} = 0$			-10	μΑ
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$			±10	μΑ
Drain-source surrender voltage	V _{DSS}	$I_D = -1 \text{ mA}, V_{GS} = 0$	-200			V
Gate threshold voltage	V _{th}	$V_{DS} = -25 \text{ V}, I_{D} = -1 \text{ mA}$	-2.0		-4.0	V
Drain-source ON resistance	R _{DS(on)}	$V_{GS} = -10 \text{ V}, I_D = -1.0 \text{ A}$		1.5	2.0	Ω
Forward transfer admittance	Y _{fs}	$V_{DS} = -25 \text{ V}, I_{D} = -1.0 \text{ A}$	1.0	1.7		S
Diode forward voltage	V_{DF}	$I_{DR} = -2.0 \text{ A}, V_{GS} = 0$			1.4	V
Short-circuit forward transfer capacitance (Common source)	C _{iss}	$V_{DS} = -20 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		400		pF
Short-circuit output capacitance (Common source)	C _{oss}			55		pF
Reverse transfer capacitance (Common source)	C _{rss}			25		pF
Turn-on delay time	t _{d(on)}	$V_{DD} = 100 \text{ V}, I_D = -1.0 \text{ A}, R_L = 100 \Omega$		12		ns
Rise time	t _r	$V_{GS} = -10 \text{ V}$		15		ns
Turn-off delay time	t _{d(off)}			50		ns
Fall time	t _f			25		ns
Thermal resistance (ch-c)	R _{th(ch-c)}				12.5	°C/W
Thermal resistance (ch-a)	R _{th(ch-a)}				125	°C/W

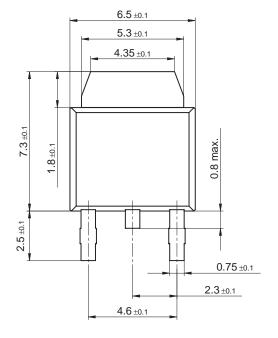
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

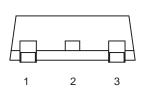


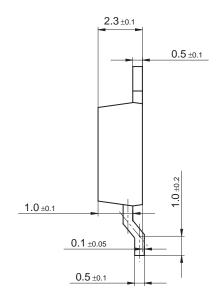


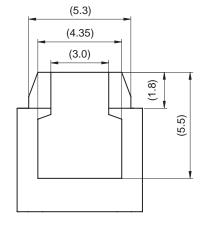
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U-G2 Unit: mm









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